



ZVP2110G

SOT223 P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C	
-100V	8Ω @ V _{GS} = 10V	-310mA	

Features and Benefits

- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

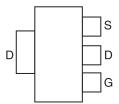
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.112 grams (Approximate)

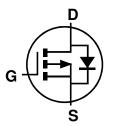
SOT223



Top View



Pin Out Top-View



Equivalent Circuit

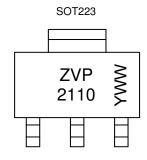
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
ZVP2110GTA	Standard	SOT223	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZVP 2110 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I _D	-310	mA
Pulsed Drain Current	I _{DM}	-3	Α

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25 °C	P _{tot}	2	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	.€

Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	$I_D = -1 \text{mA}, V_{GS} = 0 \text{V}$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1 -100	μΑ	$\begin{aligned} &V_{DS} = \text{-}100\text{V}, V_{GS} = 0\text{V} \\ &V_{DS} = \text{-}80\text{V}, V_{GS} = 0\text{V} , T = +125\text{°C} \\ &(\text{Notes 6}) \end{aligned}$	
Gate-Body Leakage	I _{GSS}	_		-20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	_	-3.5	V	$I_D = -1mA$, $V_{DS} = V_{GS}$	
ON CHARACTERISTICS							
On-State Drain Current (Note 5)	$I_{D(on)}$	-750			mA	$V_{DS} = -25V, V_{GS} = -10V$	
Static Drain-Source On-State Resistance (Note 5)	R _{DS (ON)}	_		8	Ω	$V_{GS} = -10V, I_D = -375mA$	
Forward Transconductance (Notes 5 & 6)	g fs	125	_	_	mS	$V_{DS} = -25V, I_{D} = -375mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 6)	Ciss	_		100	pF	V 05 V V 0V	
Output Capacitance (Note 6)	Coss	_	_	35	pF	V _{DS} = -25 V, V _{GS} = 0V -f = 1MHz	
Reverse Transfer Capacitance (Note 6)	C_{rss}	_	_	10	pF		
Turn-On Delay Time (Notes 6 & 7)	t _{d(on)}	_	_	7	ns	- V _{DD} ≈ -25V, I _D = -375mA	
Turn-On Rise Time (Notes 6 & 7)	t _r	_	_	15	ns		
Turn-Off Delay Time (Notes 6 & 7)	t _{d(off)}	_		12	Ns		
Turn-Off Fall Time (Notes 6 & 7)	t _f	_	_	15	Ns		

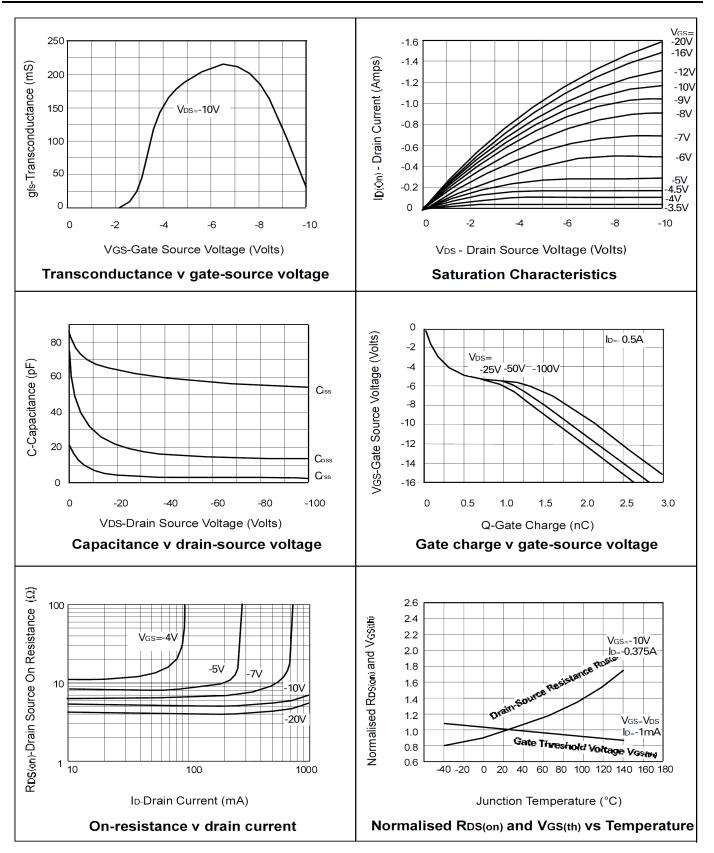
Notes: 5. Measured under pulsed conditions. Width = 300μ s. Duty cycle $\leq 2\%$.

Sample Test

^{7.} Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator.



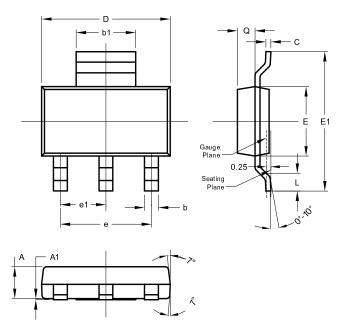
Typical Characteristics





Package Outline Dimensions

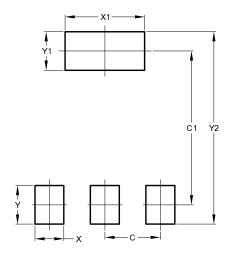
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
C2	8 00



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